International
IOR Rectifier

Bulletin I0123J rev. A 02/97

IR350DM..CCB SERIES

STANDARD RECOVERY DIODES

- **Junction Size:** **Square 350 mils**
- **Wafer Size:** **4"**
- **V_{RRM} Class:** **800 and 1200 V**
- **Passivation Process:** **Glassivated MOAT**
- **Reference IR Packaged Part:** **IRKD71 Series**

Major Ratings and Characteristics

Parameters		Units	Test Conditions
V_{FM}	Maximum Forward Voltage	960 mV	T_J = 25°C, I_F = 25 A
V_{RRM}	Reverse Breakdown Voltage Range	800 and 1200 V	T_J = 25°C, I_{RRM} = 100 µA **(1)**

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 µm)
Chip Dimensions	350 x 350 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	300 µm, ± 10 µm
Maximum Width of Sawing Line	45 µm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code

IR	350	D	M	12	C	CB
1	2	3	4	5	6	7

1 - International Rectifier Device

2 - Chip Dimension in Mils

3 - Type of Device: D = Wire Bondable Standard Recovery Diode

4 - Passivation Process: M = Glassivated MOAT

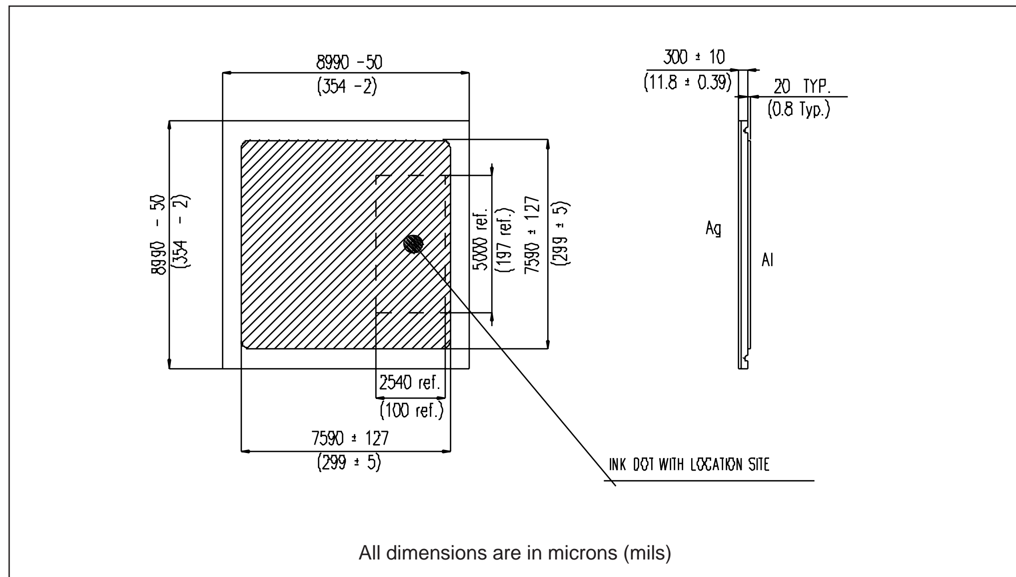
5 - Voltage code: Code x 100 = V_{RRM}

6 - Metallization: C = Aluminium (Anode) - Silver (Cathode)

7 - CB = Probed Uncut Die (wafer in box)
None = Probed Die in chip carrier

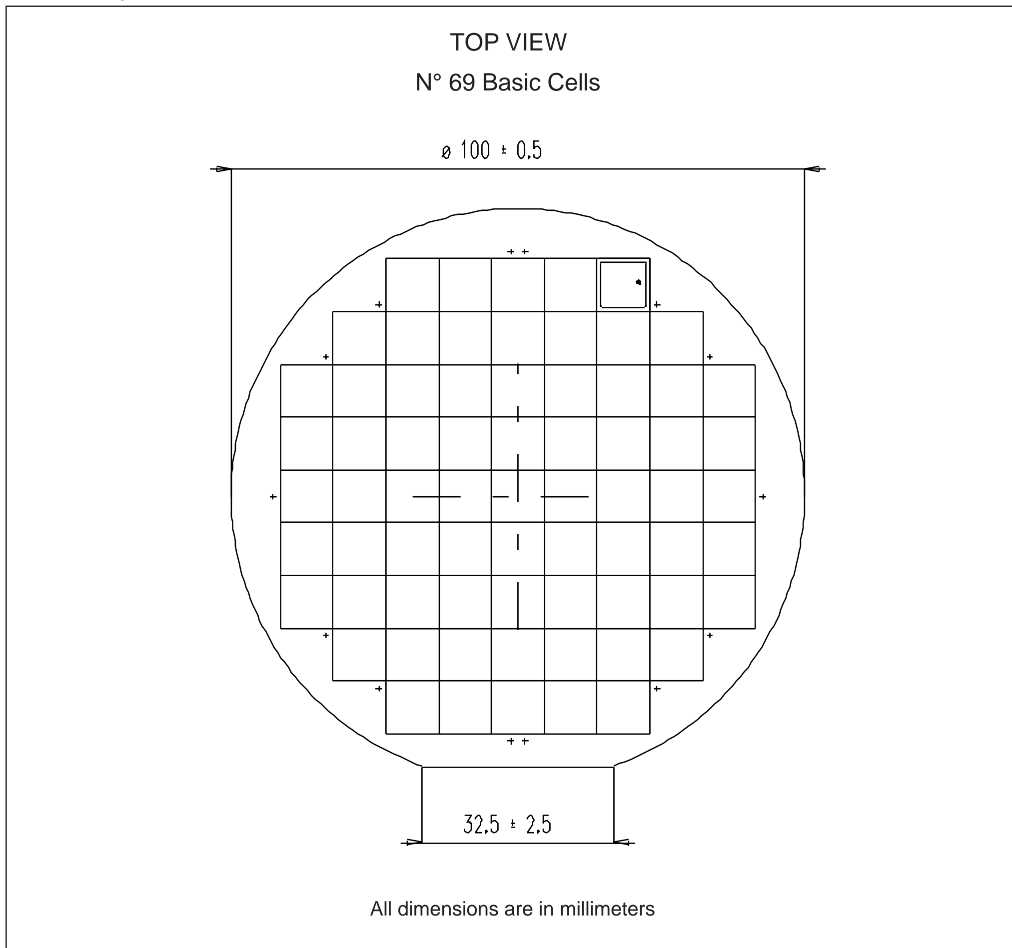
Available Class	
08 =	800 V
12 =	1200 V

Outline Table



All dimensions are in microns (mils)

Wafer Layout



All dimensions are in millimeters